

Absolute Maximum Ratings

| Parameter | Symbol | Value | Unit |
|------------------------------|-----------|----------|------|
| Collector-Emitter Voltage | V_{CES} | 1350 | V |
| Gate-Emitter Voltage | V_{GES} | ± 25 | V |
| Continuous Collector Current | T_C | | |
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Electrical Characteristics $T_{vj}=25^{\circ}\text{C}$, unless otherwise noted

| Parameter | Symbol | Test condition | Min. | Typ. | Max. | Unit |
|---------------------------|--------------|--|------|------|------|------|
| SWITCHING (Note 2) | | | | | | |
| Turn-Off Delay Time | $t_{d(off)}$ | $V_{CC} = 600\text{V}, I_C = 15\text{A}$ $R_G = 5 \text{ } , V_{GE} = 15\text{V}$ Inductive Load, $T_{vj} = 25$ | -- | 113 | -- | ns |
| Fall Time | t_f | | -- | 106 | 159 | ns |
| Turn-Off Switching Loss | E_{OFF} | | -- | 0.38 | 0.57 | mJ |
| Turn-Off Delay Time | $t_{d(off)}$ | $V_{CC} = 600\text{V}, I_C = 15\text{A}$ $R_G = 5 \text{ } , V_{GE} = 15\text{V}$ Inductive Load, $T_{vj} = 175$ | -- | 131 | -- | ns |
| Fall Time | t_f | | -- | 213 | -- | ns |
| Turn-Off Switching Loss | E_{OFF} | | -- | 0.70 | 1.05 | mJ |
| Turn-Off Delay Time | $t_{d(off)}$ | $V_{CC} = 600\text{V}, I_C = 30\text{A}$ $R_G = 5 \text{ } , V_{GE} = 15\text{V}$ Inductive Load, $T_{vj} = 25$ | -- | 113 | -- | ns |
| Fall Time | t_f | | -- | 105 | 157 | ns |
| Turn-Off Switching Loss | E_{OFF} | | -- | 0.81 | 1.22 | mJ |
| Turn-Off Delay Time | $t_{d(off)}$ | $V_{CC} = 600\text{V}, I_C = 30\text{A}$ $R_G = 5 \text{ } , V_{GE} = 15\text{V}$ Inductive Load, $T_{vj} = 175$ | -- | 123 | -- | ns |
| Fall Time | t_f | | -- | 220 | -- | ns |
| Turn-Off Switching Loss | E_{OFF} | | -- | 1.52 | 2.28 | mJ |

Notes :

(2) Not subject to production test verified by design/characterization

Device Characteristics

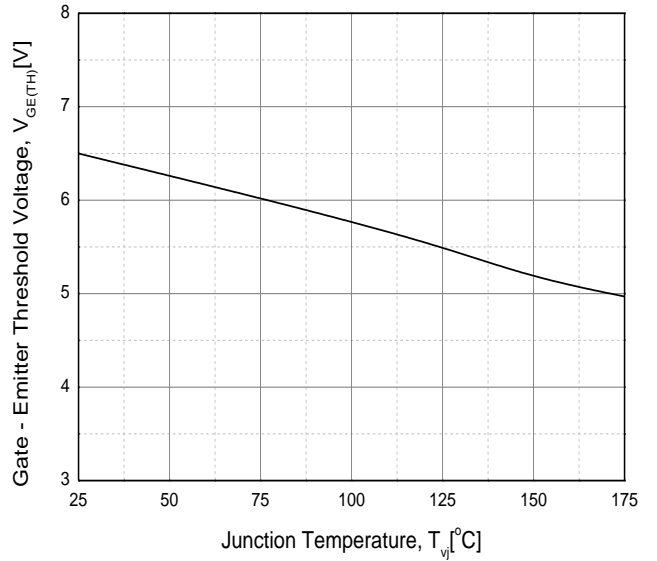
Fig. 1 IGBT Output Characteristics



Fig. 2 IGBT Output Characteristics



Fig. 3 IGBT Saturation Voltage vs. Junction Temperature Fig. 4 IGBT Threshold Voltage vs. Junction Temperature



Device Characteristics

Fig. 5 IGBT Transfer Characteristic

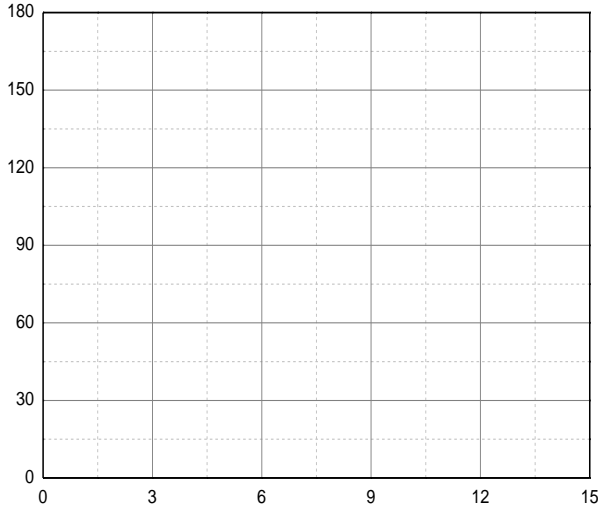


Fig. 6 IGBT Capacitance Characteristics



Fig. 7 Diode Conduction Characteristics

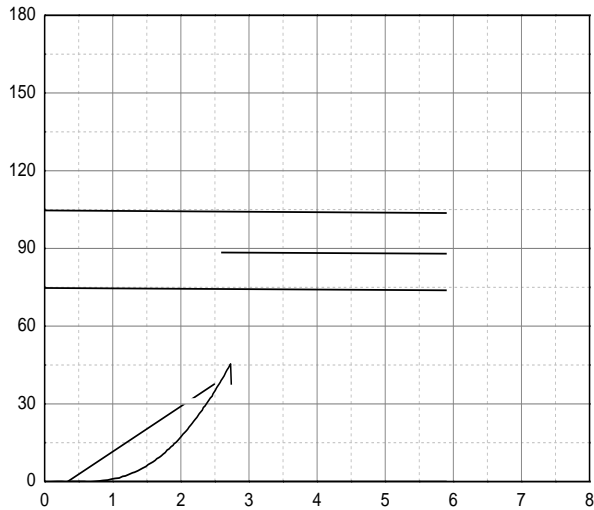
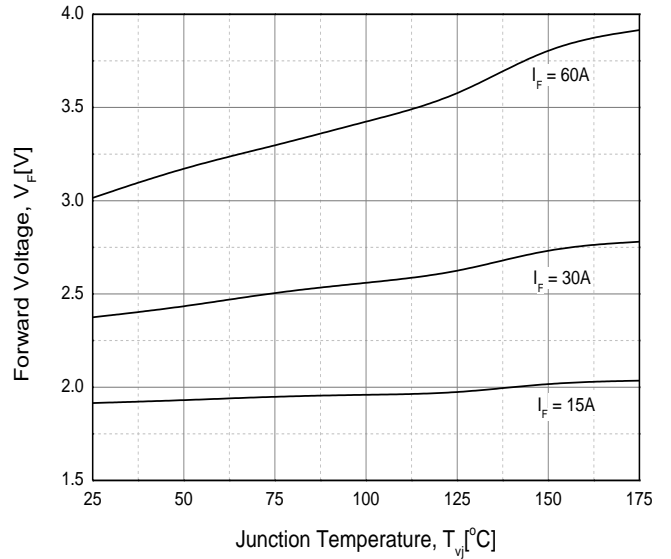


Fig. 8 Diode Forward Voltage vs. Junction Temperature



Device Characteristics

Fig. 9 Turn-off Time vs. Gate Resistor

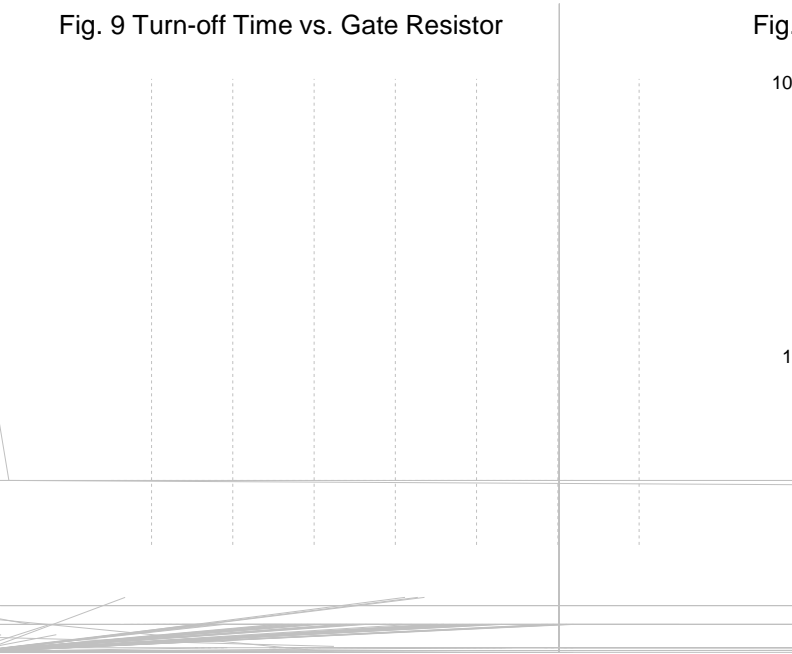


Fig. 10 Turn-off Time vs. Collector Current

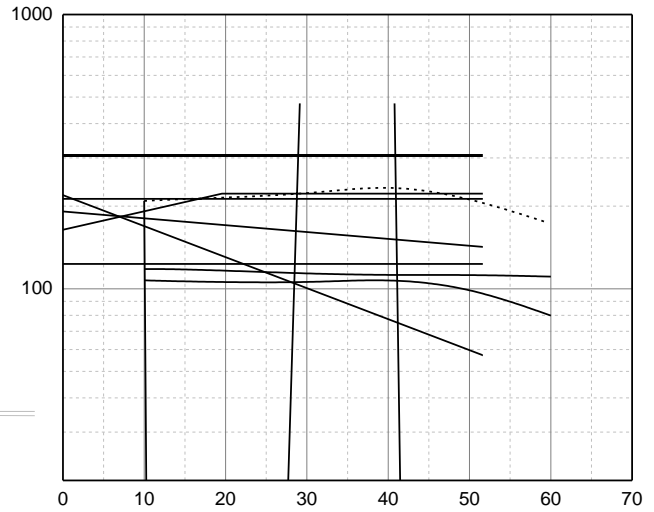


Fig. 11 Turn-off Loss vs. Gate Resistor

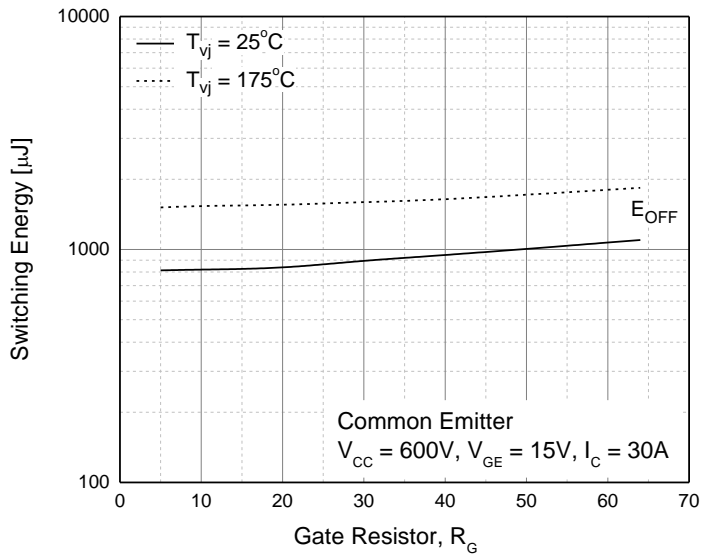
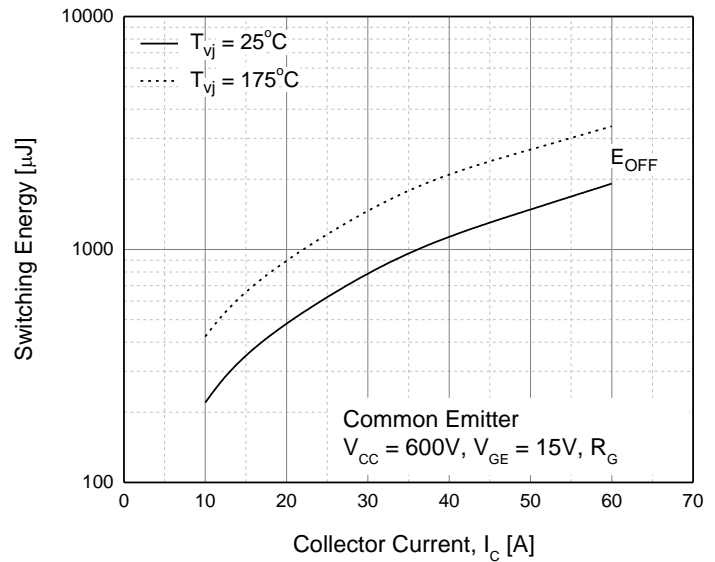
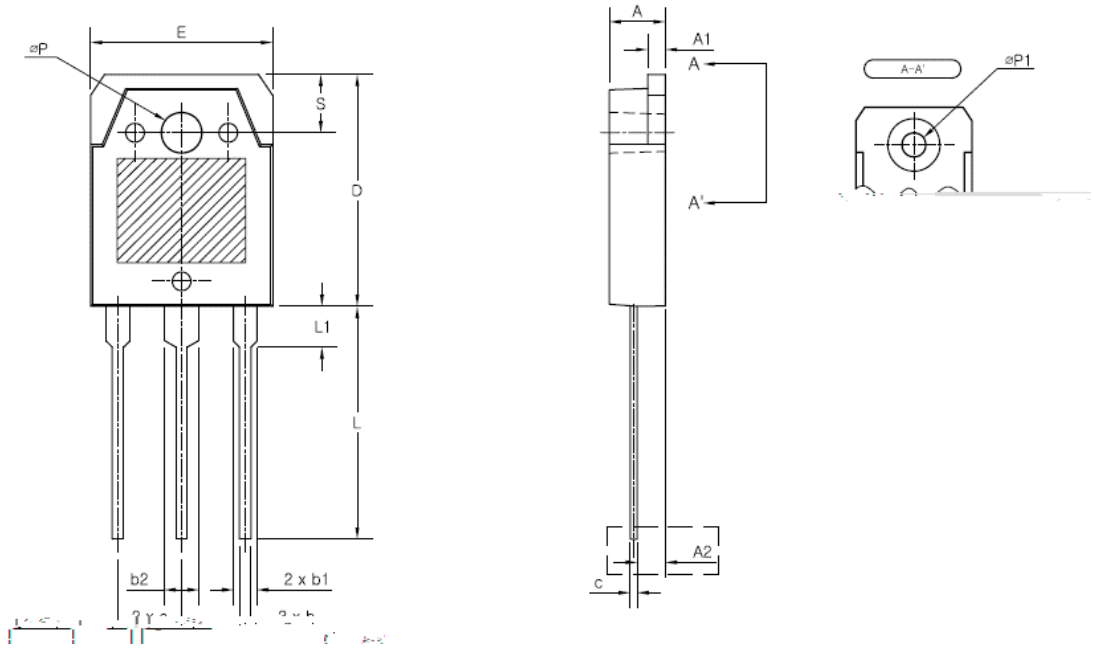


Fig. 12 Turn-off Loss vs. Collector Current





TO-3PN MECHANICAL DATA



| SYMBOL | mm | | |
|--------|-------|-------|-------|
| | MIN | NOM | MAX |
| A | 4.6 | 4.8 | 5 |
| A1 | 1.45 | 1.5 | 1.65 |
| A2 | 2.2 | 2.4 | 2.6 |
| b | 0.8 | 1 | 1.2 |
| b1 | 2.8 | 3 | 3.2 |
| b2 | 1.8 | 2 | 2.2 |
| c | 0.55 | 0.6 | 0.75 |
| D | 19.20 | 19.65 | 20.10 |
| E | 15.4 | 15.6 | 15.8 |
| e | 5.15 | 5.45 | 5.75 |
| L | 19.8 | 20 | 20.2 |
| L1 | 3.3 | 3.5 | 3.7 |
| P | 3.5 | | |
| P1 | 3.2 | | |
| S | 5 | | |

Disclaimer

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